

2017 IEEE SOI-3D-Subthreshold Microelectronics Technology Unified Conference (S3S 2017)

**Burlingame, California, USA
16 – 19 October 2017**



**IEEE Catalog Number: CFP17SOI-POD
ISBN: 978-1-5386-3767-8**

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IEEE Catalog Number:	CFP17SOI-POD
ISBN (Print-On-Demand):	978-1-5386-3767-8
ISBN (Online):	978-1-5386-3766-1
ISSN:	1078-621X

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SESSION 1: PLENARY SPEAKERS

Session Chairs:

Frederic Allibert, Soitec
Ali Khakifirooz, Intel

- 1.1 **3D NAND and 3D XPoint™: 3D Non-Volatile Memories Ushering in a New Era in Scaling, Performance and Applications.....N/A**
Al Fazio; Senior Fellow at Intel
- 1.2 **Ultra-low Power Semiconductor Platform Solutions for Intelligent Compute and Connect.....N/A**
Ted Letavic; Senior Fellow, GLOBALFOUNDRIES
- 1.3 **In Quest of the Next Information Processing Platform.....N/A**
Suman Datta; Chang Family Professor of Engineering Innovation, University of Notre Dame

SESSION 2: TECHNOLOGY DIRECTIONS AND ECOSYSTEM

Session Chairs:

Bruce Doris, IBM
Olivier Faynot, CEA-Leti

- 2.1 **Magnetic Tunnel Junctions for Neuromorphic and Stochastic Computing.....N/A**
Kaushik Roy; Purdue university, West Lafayette, IN, USA (Invited Speaker)
- 2.2 **Scaling the Compute and High Speed Networking Needs of the Data Center with Silicon Photonics.....N/A**
Robert Blum; Intel, Santa Clara, CA, USA (Invited Speaker)
- 2.3 **Realizing the Next Growth Wave for Semiconductors and MEMs – A New Approach to Enable Innovative Startups.....N/A**
D. Armbrust, R. Lazansky, N. Kepler and R. Goldman; Silicon Catalyst, San Jose, CA, USA (Invited Speaker)
- 2.4 **TBA.....N/A**
Howard Tang; VeriSilicon, San Jose, CA, USA (Invited Speaker)

SESSION 3: FDSOI CIRCUITS 1

Session Chairs:

Toshiro Hiramoto, University of Tokyo
Philippe Flatresse, Soitec

- 3.1 **Ultra Low Energy Cryptographic Engine Designs and SOTB Chip Fabrication Services in Japan.....1**
Makoto Ikeda, Department of Electrical Engineering and Information Systems, University of Tokyo, Bunkyo, Tokyo, Japan (Invited Paper)
- 3.2 **An Implementation of 2RW Dual-Port SRAM Using 65 nm Silicon-on-Thin-Box (SOTB) for Smart IoT.....2**
Y. Yamamoto¹, T. Hasegawa¹, M. Yabuuchi¹, K. Nii¹, Y. Sawada¹, S. Tanaka¹, Y. Shinozaki², K. Ito², H. Shinkawata¹ and S. Kamohara¹; ¹Renesas Electronics Corporation, Tokyo, Japan, ²Nippon Systemware Co. Ltd., Tokyo, Japan
- 3.3 **Power and Performance Comparision of Body Bias in 28HPC and Back Bias in 22FDX.....4**
K. Zhao, J. Wang, J. Li, B. Yang, H. Wang, M. Shen, F. Yu, L. Xu; Shanghai Fudan Microelectronics Group Company Limited, Shanghai, China

- 3.4 Level-Shifters Free Approach for Multi-V_{DD} SOTB Employing Adaptive V_t Modulation for pMOSFET.....7**
 K. Usami¹, S. Kogure¹, Y. Yoshida¹, R. Magasaki¹ and H. Amano²; ¹*Shibaura Institute of Technology, Koto-ku, Tokyo, Japan*, ²*Keio University, Kouhoku-ku, Yokohama, Japan*
- 3.5 Class AB Base-Band Amplifier Design with Body Biasing in 28nm UTBB FD-SOI CMOS.....10**
 M. Videnović-Mišić¹, P. Cathelin², A. Cathelin², B. Nikolić³; ¹*Faculty of Technical Sciences, University of Novi Sad, Novi Sad, Serbia*, ²*STMicroelectronics, Crolles, France*, ³*Berkeley Wireless Research Center, University of California, Berkeley, Berkeley, USA*

SESSION 4: ADVANCED SOI DEVICES 1

Session Chairs:

Bich-Yen Nguyen, Soitec

Bruce Doris, IBM

- 4.1 FinFETs on Insulator with Silicided Source/Drain.....13**
 H. Zhu, J. Luo, Q. Zhang, H. Yin, H. Zhong, C. Zhao; *Key Laboratory of Microelectronics Devices and Integrated Technologies, Institute of Microelectronics, Chinese Academy of Sciences and the University of Chinese Academy of Sciences, Beijing, China (Invited Speaker)*
- 4.2 First Demonstration of Symmetric Lateral NPN Transistors on SOI Featuring Epitaxially-Grown Emitter/Collector Regions.....15**
 P. Hashemi, J.-B. Yau, K. K. Chan, T. H. Ning and G. G. Shahidi; *IBM Research Thomas J. Watson Research Center, Yorktown Heights, New York, USA*
- 4.3 Gate Controlled Diode Characteristics of Super Steep Subthreshold Slope PN-Body Tied SOI-FET for High Efficiency RF Energy Harvesting.....17**
 S. Momose¹, J. Ida¹, T. Mori¹, T. Yoshida¹, J. Iwata¹, T. Horii¹, T. Furuta¹, K. Itoh¹, K. Ishibashi², and Y. Arai³; ¹*Division of Electrical Engineering, Kanazawa Institute of Technology, Ishikawa, Japan*, ²*The University of Electro-Communications, Tokyo, Japan*, ³*High Energy Accelerator Research Org. KEK, Tsukuba, Japan*
- 4.4 A Novel Photodetector Based on the Interface Coupling Effect in Silicon-on-Insulator MOSFETs.....20**
 JN. Deng¹, JH. Shao¹, BR. Lu¹, YF. Chen¹, A. Zaslavsky², S. Cristoloveanu³, M. Bawedin³ and J. Wan¹; ¹*State Key Lab of ASICs and Systems, School of Information Science and Engineering, Fudan University, Shanghai, China*, ²*Department of Physics and School of Engineering, Brown University, Providence, Rhode Island, USA*, ³*IMEP-LAHC, INP-Grenoble/Minatex, Grenoble, France*

SESSION 5: MONOLITHIC 3D 1

Session Chairs:

Olivier Faynot, CEA-Leti
Heinz Schmid, IBM

- 5.1 3D Nanomagnetic Logic: How Far Beyond CMOS?.....23**
M. Becherer¹, G. Csaba², G. Žiemys³; ¹Nanoelectronics Technical University Munich, Munich, Germany, ²Pazmany Peter Catholic University, Budapest, Hungary, ³Technical Electronics Technical University Munich, Munich Germany (Invited Speaker)
- 5.2 Vertically-Composed Fine-Grained 3D CMOS.....25**
M. Li¹, J. Shi¹, M. Rahman², S. Khasanvis³, S. Bhat¹, C. A. Moritz¹; ¹Electrical and Computer Engineering, University of Massachusetts, USA, ²Computer Science and Electrical Engineering, University of Missouri, USA, ³BlueRISC Inc. USA (Invited Speaker)
- 5.3 Double-Gate Si Junction-less n-Type Transistor for High Performance Cu-BEOL Compatible Applications Using 3D Sequential Integration.....27**
A. Vandooren, L. Witters, E. Vecchio, E. Kunnen, G. Hellings, L. Peng, F. Inoue, W. Li, N. Waldron, D. Mocuta, N. Collaert; IMEC, Leuven, Belgium
- 5.4 Cost Projections and Benefits for Transistor-Level 3-D Integration with Stacked Nanowires.....29**
N. K. Macha, M. Rahman; Department of Computer Science & Electrical Engineering, University of Missouri Kansas City, Missouri, USA

SESSION 6: MODELING AND CHARACTERIZATION

Session Chairs:

Nobuyuki Sugii, Hitachi, Ltd.
Joao Antonio Martino, University of São Paulo

- 6.1 Investigations on Contact Punch-Through in 28 nm FDSOI through Virtual Fabrication.....32**
B. Vianne¹, P. Morin¹, C. Beylier¹, J.-C. Giraudin¹, S. Desmoulins¹, R. Gonella¹, A. Juncker², D. Fried²; ¹STMicroelectronics, Crolles Cedex, France, ²Coventor, Inc, Waltham, Massachusetts, USA
- 6.2 New Method for Individual Electrical Characterization of Stacked SOI Nanowire MOSFETs.....34**
B. C. Paz¹, M. Cassé², S. Barraud², G. Reimbold², M. Vinet², O. Faynot² and M. A. Pavanello¹; ¹Centro Universitário FEI, São Bernardo do Campo, Brazil, ²CEA, LETI, MINATEC Campus, Grenoble, France
- 6.3 Advanced Characterization Technique for the Extraction of Intrinsic Effective Mobility in Ultra-Thin-Body Strained SOI MOSFETs.....37**
M. Seo^{1,2}, H. Bae¹, C.-H. Jeon², B.-H. Lee² and Y.-K. Choi¹; ¹School of Electrical Engineering, Korea Advanced Institute of Science and Technology Daejeon, Republic of Korea, ²Semiconductor Business Samsung Electronics, Yongin-Si, Gyeonggi-Do, Republic of Korea
- 6.4 Self-Heating Assessment and Cold Current Extraction in FDSOI MOSFETs.....39**
K. Triantopoulos^{1,2}, M. Cassé¹, L. Brunet¹, P. Batude¹, C. Fenouillet-Béranger¹, G. Reimbold¹, G. Ghibaudo²; ¹CEA, LETI, MINATEC Campus, Grenoble, France, ²IMEP-LAHC, Grenoble, France

6.5 Z²-FET SPICE Model: DC and Memory Operation.....42

S. Martinie¹, J. Lacord¹, O. Rozeau¹, M.-S. Parihar², K. Lee², M. Bawedin², S. Cristoloveanu², Y. Taur³ and J.-C. Barbe¹; ¹CEA-LETI, Grenoble, France. ²University Grenoble Alpes, IMEP-LAHC, Grenoble INP Minatec, Grenoble, France. ³University of California, San Diego, USA

6.6 An Improved Mobility Model for FDSOI TriGate and Other Multi-Gate Nanowire MOSFETs Down to Nanometer-Scaled Dimensions.....45

M. Cassé¹, J. Pelloux-Prayer¹, Z. Zeng², Y.-M. Niquet², F. Triozon¹, S. Barraud¹, G. Reimbold¹; ¹CEA, LETI, MINATEC Campus, Grenoble, France, ²INAC-MEM, LSIM, Grenoble, France

SESSION 7: 3D WAFER STACKING

Session Chairs:

Markus Becherer, Nanoelectronics Technical University Munich

Zvi Or-Bach, MonolithIC 3D

7.1 Heterogeneous Platform.....N/A

Sergey Shumarayev; Intel, CA, USA (Invited Speaker)

7.2 Heterogeneous Integration toward Monolithic 3D Chip.....48

S.H. Kim¹, S.-K. Kim¹, J.-P. Shim¹, D.-M. Geum¹, G. Ju¹, H. S. Kim¹, H. J. Lim¹, H. R. Lim¹, J.-H. Han¹, C.M. Kang², D. S. Lee², J. D. Song¹, W. J. Choi¹, H.-J. Kim¹; ¹Korea Institute of Science and Technology (KIST), Korea, ²Gwangju Institute of Science and Technology (GIST), Korea (Invited Speaker)

7.3 Integration of Si-CMOS and III-V Materials through Multi-Wafer Stacking.....50

K. H. Lee¹, L. Zhang¹, B. Wang¹, S. C. Goh¹, S. Bao^{1,2}, Y. Wang¹, W. A. Sasangka¹, K. E. K. Lee¹, E. Fitzgerald^{1,3}, and C. S. Tan^{1,2}; ¹Singapore-MIT Alliance for Research and Technology (SMART), Singapore, ²School of Electrical and Electronic Engineering, Nanyang Technological University, Singapore, ³Department of Materials Science and Engineering, Massachusetts Institute of Technology, Cambridge, Massachusetts, USA

7.4 A Novel In-Situ Resistance Measurement to Extract IMC Resistivity and Kinetic Parameter for CoSn 3D Stacks.....52

L. Hou^{1,2}, J. Derakhshandeh¹, J. De Coster¹, T. Wang¹, V. Cherman¹, P. Bex¹, K. J. Rebibis¹, G. Van De Plas¹, G. Beyer¹, E. Beyne¹, I. De Wolf^{1,2}; ¹IMEC, Leuven, Belgium, ²Dept. Material Engineering, KU Leuven, Leuven, Belgium

7.5 Three Dimensional Monolithic System on a Chip(3DSoC).....N/A

Linton Salmon; DARPA, Arlington, VA, USA (Invited Speaker)

SESSION 8: POSTER SESSION

Session Chairs:

Michelly de Souza, Centro Universitário FEI

Pauline Paki, DTRA

- 8.1 Low Temperature Influence on Long Channel STI Last Process Relaxed and Strained Ge pFinFETs.....55**
A.V. Oliveira^{1,2}, P.G.D. Agopian^{2,4}, J.A. Martino², E. Simoen³, J. Mitard³, L. Witters³, N. Collaert³ and C. Claeys³; ¹UTFPR, Campus Toledo, Brazil, ²LSI/PSI/USP, University of São Paulo, São Paulo, Brazil, ³Imec, Leuven, Belgium, ⁴UNESP, Campus de São João da Boa Vista, Brazil, ⁵E.E. Dept., KU Leuven, Belgium
- 8.2 Impact of the Zn Diffusion Process at the Source Side of In_xGa_{1-x}As nTFETs on the Analog Parameters Down to 10 K.....58**
C. Bordallo¹, J. Martino¹, P. Agopian^{1,2}, A. Alian³, Y. Mols³, R. Rooyackers³, A. Vandooren³, A. Verhulst³, E. Simoen³, C. Claeys^{3,4}, N. Collaert³; ¹LSI/PSI/USP, University of São Paulo, São Paulo, Brazil, ²UNESP, Univ. Estadual Paulista, São João da Boa Vista, Brazil, ³Imec, Leuven, Belgium, ⁴E.E. Dept., KU Leuven, Leuven, Belgium
- 8.3 Ultra Low Power Inductorless Low Noise Amplifier: Comparison of FDSOI Technologies.....61**
J. Zaini^{1,2}, F. Hameau¹, T. Taris², D. Morche¹ and P. Audebert¹; ¹CEA, LETI, MINATEC Campus, Grenoble, France, ²IMS Laboratory, University of Bordeaux, Talence, France
- 8.4 Is there a Zero Temperature Bias Point (ZTC) on Back Enhanced (BE) SOI MOSFET?.....63**
L. S. Yojo¹, R. C. Rangel^{1,2}, K. R. A. Sasaki¹, J. A. Martino¹; ¹LSI/PSI/USP, University of São Paulo, São Paulo, Brazil, ²FATEC-SP, Faculdade de Tecnologia de São Paulo, São Paulo, Brazil
- 8.5 New Method for Observing Self-Heating Effect Using Transistor Efficiency Signature.....66**
C. A. B. Mori¹, P. G. D. Agopian^{1,2}, J. A. Martino¹; ¹LSI/PSI/USP, University of São Paulo, São Paulo, Brazil, ²São Paulo State University (UNESP), São João da Boa Vista, Brazil
- 8.6 Lateral Spacers Influence on the Effective Channel Length of Junctionless Nanowire Transistors.....69**
R. Trevisoli, R. T. Doria, M. de Souza, M. A. Pavanello; Electrical Engineering Department, Centro Universitário FEI São Bernardo do Campo, Brazil
- 8.7 Definite Influence of Substrate-Contact Condition on SOI Substrate Impedance Parameters.....72**
I. Yarita, S. Shingo and Y. Omura; Kansai University, Suita, Osaka, Japan
- 8.8 Study of Process Transconductance for Understanding Gate Capacitance of FDSOI NCFET.....74**
S. Qureshi and S. Mehrotra; Department of Electrical Engineering, Indian Institute of Technology Kanpur, India
- 8.9 Improving Solder Wetting of Micro Bumps on Metal Pads Using Metallic or Organic Pad Coatings.....77**
I. De Preter, L. Hou, J. Derakhshandeh, P. Bex, F. Fodor, V. Cherman, K. J. Rebibis, A. Miller, G. Beyer, E. Beyne; IMEC, Leuven, Belgium
- 8.10 PVT Compensation in Mie Fujitsu 55 nm DDC: A Standard-Cell Library Based Comparison.....79**
T. C. Müller^{1,2}, J-L. Nagel¹, M. Pons¹, D. Séverac¹, K. Hashiba³, S. Sawada³, K. Miyatake³, S. Emery¹, A. Burg²; ¹CSEM, Neuchâtel, Neuchâtel, Switzerland, ²École polytechnique fédérale de Lausanne, Lausanne, Vaud, Switzerland, ³Mie Fujitsu Semiconductor Ltd., Yokohama, Kanagawa, Japan

- 8.11 Theoretical Models for Low-Frequency Noise Behaviors of Buried-Channel MOSFETs.....81**
Y. Omura and S. Sato; *Dept. of Electric, Electronics and Information Eng., Kansai University and ORDIST of Kansai University, Yamate-cho, Suita, Osaka, Japan*
- 8.12 14nm FinFET Technology SRAM Cell Margin Evaluation and Analysis by Local Layout Effect.....83**
S.Y. Mun¹, D. Burnett², K.Y. Lim¹, S. Parihar², Y.J. Shi¹, H.C. Lo¹, W. Hong¹, K.J. Lee¹, O. Hu¹, J. Versaggi¹, C. Jerome¹, J.G. Lee¹, S. B. Samavedam¹, D.K. Sohn¹; ¹ATD 14NM Device, GLOBALFOUNDRIES, Malta, NY, USA, ²Global Memory Solutions, GLOBALFOUNDRIES, Austin, TX, USA
- 8.13 Design Optimization for NEM Relays Implemented in BEOL Layers.....85**
U. Sikder, T-J. King Liu; *Intel Department of EECS, University of California, Berkeley, CA, USA*
- 8.14 Energy-Delay Tradeoffs of Low-Voltage Dual Mode Logic in 28nm FD-SOI.....88**
R. Taco¹, I. Levi¹, M. Lanuzza², A. Fish¹; ¹Bar-Ilan University, Ramat-Gan, Israel, ²Univeristy of Calabria, Rende, Italy
- 8.15 A 2.9nW Ultra-Low Power Ripple-Voltage MPPT for Autonomous Miniature Sensor Nodes.....91**
K. Lundager, and F. Moradi; *Department of Electrical and Computer Engineering, Aarhus University, Aarhus, Denmark*
- 8.16 Hump-Effect Impact on Subthreshold VLSI Circuit.....93**
M.Coustans¹, D. Gauthey², S. Rota², A. Acovic³, P. Habas³, R. Meyer³; ¹Swiss Federal Institute of Technology (EPFL) Lausanne, Switzerland, ²The Swatch Group Research and Development Ltd, Marin-Epagnier, Switzerland, ³EM Microelectronic-Marin SA, Marin-Epagnier, Switzerland
- 8.17 Differential Input Output CMOS (DINO-CMOS) – High performance and Energy Efficient Logic Family.....96**
M. Haber¹, I. Levi¹, Y. Yehoshua² and A. Fish²; ¹Student Member IEEE, ²Member IEEE
- 8.18 Secured Dual-Rail-Precharge Mux-Based (DPMUX) Symmetric-Logic for Low Voltage Applications.....99**
D. Z. Zabib, I. Levi, A. Fish, O. Keren; *Faculty of Engineering, Bar-Ilan University, Israel*
- 8.19 STI Techniques for Isolation of RF-SOI Devices.....101**
S. P. Adusumilli, S. M. Shank, J. Ellis-Monaghan, C-H. Teng, M. D. Levy, A. K. Stamper; *RF Technology Development, Fab 9, GLOBALFOUNDRIES, Essex Junction Vt, USA*

SESSION 9: RF CIRCUITS

Session Chairs:

Frederic Allibert, Soitec
Mostafa Emam, Incize

- 9.1 Opportunity of CMOS FD-SOI for RF Power Amplifier.....103**
B. Martineau, E. Mercier and P. Vincent; *CEA-LETI, Grenoble, France Université de Grenoble-Alpes, Grenoble, France*
- 9.2 A High-Efficiency Single-Stage Power Amplifier for WLAN 802.11ac in 22nm FDSOI.....105**
S. T. Lee, A. Bellaouar and S. Embabi; *GLOBALFOUNDRIES, Richardson, TX, USA*
- 9.3 A Study of Interferences Inside an RF Switch Array in 45nm SOI CMOS.....107**
C. Wang¹, F. Lu¹, Q. Chen¹, F. Zhang¹, C. Li¹, D. Wang², and A. Wang¹; ¹*Department of Electrical and Computer Engineering, University of California, Riverside, CA, USA;* ²*GLOBALFOUNDRIES, USA*
- 9.4 Improving Noise and Linearity of CMOS Wideband Inductorless Balun LNAs for 10-GHz Software-Defined Radios in 28nm FDSOI.....110**
C. Gimeno, F. Stas, G. de Streel, D. Bol, and D. Flandre; *ICTEAM Institute, Université Catholique de Louvain, Louvain-la-Neuve, Belgium*
- 9.5 A Wide Range 60 GHz VCO Using Back-Gate Controlled Varactor in 22 nm FDSOI Technology.....112**
C. Zhang¹ and M. Otto²; ¹*GLOBALFOUNDRIES, Austin, TX, USA,* ²*GLOBALFOUNDRIES, Dresden, Germany*

SESSION 10: EMBEDDED MEMORIES

Session Chairs:

Nuo Xu, Samsung
Jamie Schaeffer, GLOBALFOUNDRIES

- 10.1 Physical and Circuit Modeling of HfO₂ Based Ferroelectric Memories and Devices.....115**
M. Pesic¹, V. Di Lecce², M. Hoffmann¹, H. Mulaosmanovic¹, B. Max⁴, U. Schroeder¹, S. Slesazeck¹, L. Larcher^{2,3}, T. Mikolajick^{1,4}; ¹*NaMLab, Dresden, Germany,* ²*MDLSoft, Santa Clara, CA, USA,* ³*DISMI, University of Modena and Reggio Emilia, Reggio Emilia, Italy,* ⁴*Chair of Nanoelectronic Materials, Technische Universität Dresden, Dresden, Germany (Invited Speaker)*
- 10.2 Review of Progress in Understanding the Electron Transport Properties of Amorphous Chalcogenide Phase Change Semiconductors.....119**
J. Liu; *Department of Electrical Engineering, University of Washington, Seattle, WA, USA (Invited Speaker)*
- 10.3 STT-MRAM for Embedded Memory Applications from eNVM to Last Level Cache.....123**
L. Thomas, G. Jan, S. Le, S. Serrano-Guisan, Y-J. Lee, H. Liu, J. Zhu, J. Iwata-Harms, R-Y. Tong, S. Patel, V. Sundar, D. Shen, Y. Yang, R. He, J. Haq, Z. Teng, V. Lam, P. Liu, Y-J. Wang, T. Zhong, and P-K. Wang; *TDK-Headway Technologies Inc., Milpitas, CA, USA (Invited Speaker)*
- 10.4 32Kb Innovative Fuse (I-Fuse) Array in 22nm FD-SOI with 0.9V/1.4mA Program Voltage/Current and 0.744um² Cell.....127**
S. Chung, W-K. Fang, J. Lin, W-H. Yu, and JY Hsiao; *Attopsemi Technology Co., LTD, Hsinchu, Taiwan*

SESSION 11: SOI WAFERS

Session Chairs:

Joao Antonio Martino, University of São Paulo

Bruce Doris, IBM

- 11.1 Novel CV/GV Technique for Top and Bottom BOX Interfaces Traps Density Extraction on FDSOI Wafers.....129**
W. Vandendaele¹, C. Malaquin², A. Ghorbel², M. Cassé¹, F. Allibert², G. Reimbold¹;
¹CEA LETI - MINATEC Campus, Grenoble, France, ²SOITEC SA, Parc Technologique des Fontaines, Bernin, France
- 11.2 A SPDT RF Switch Small- and Large-Signal Characteristics on TR-HR SOI Substrates.....132**
B.Kazemi Esfeh¹, S. Makovejev², F. Allibert³ and J.-P. Raskin¹; ¹ICTEAM, Université catholique de Louvain, Louvain-la-Neuve, Belgium, ²Incize, Louvain-la-Neuve, Belgium, ³Soitec, Bernin, France
- 11.3 Time-Dependent Vth Shift of Silicon on Thin BOX under Large Back Bias.....135**
Y. Yamamoto, H. Makiyama, T. Hasegawa, S. Okanishi, K. Maekawa, H. Shinkawata and Y. Yamaguchi; Renesas Electronics Corporation, Device Technology Division, Advanced Device Technology Department, Hitachinaka-shi Ibaraki, Japan
- 11.4 Enhanced Silicon-On-Insulator Platform Enabling New Structures and Applications.....137**
A. Haapalinna¹, T. Aalto²; ¹Okmetic Oy, Vantaa, Finland, ²VTT, Espoo, Finland
- 11.5 Extraction of SOI Thickness Deviation based on Resonant Wavelength Analysis for Silicon Photonics Devices.....140**
T. Horikawa^{1,2}, D. Shimura¹, H. Takahashi¹, J. Ushida¹, Y. Sobu¹, A. Shiina¹, M. Tokushima¹, S.-H. Jeong¹, K. Kinoshita¹, and T. Mogami²; ¹Photonics Electronics Technology Research Association (PETRA), Tsukuba, Japan, ²National Institute of Advanced Industrial Science and Technology (AIST), Tsukuba, Japan.

SESSION 12: LOW POWER CIRCUITS 1

Session Chairs:

Lauri Koskinen, University of Turku

Philippe Flatresse, Soitec

- 12.1 SNM Analytical Approach to Robust Subthreshold SRAM Operation based on the 55nm DDC Technology.....143**
N. Misawa¹, H. Kurata¹, K. Kumeno¹, R. Nanjo¹, M. Kai¹, T. Ema¹ and M. Pons Sole²;
¹Mie Fujitsu Semiconductor Ltd., Kuwana Mie, Japan, ²CSEM, Neuchâtel, Neuchâtel, Switzerland (Invited Speaker)
- 12.2 A 28 nW CMOS Supply Voltage Monitor for Adaptive Ultra-Low Power IoT Chips.....N/A**
D. A. Kamakshi, H. N. Patel, A. Roy, and B. H. Calhoun; Dept. of Electrical Engineering, University of Virginia, Charlottesville, Virginia, USA
- 12.3 Design Margin Elimination Through Robust Timing Error Detection at Ultra-Low Voltage.....145**
H. Reyserhove and W. Dehaene; KU Leuven, ESAT-MICAS, Kasteelpark Arenberg, Leuven, Belgium

- 12.4 A Subthreshold 30pJ/bit Self-timed Ring Based True Random Number Generator for Internet of Everything.....148**
M. Coustans¹, C. Terrier², T. Eberhardt², S. Salgado², A. Cherkaoui³, L. Fesquet³;
¹Swiss Federal Institute of Technology (EPFL), Lausanne, Switzerland, ²EM Microelectronic-Marin SA, Marin-Epagnier, Switzerland, ³Univ. Grenoble Alpes & CNRS, TIMA, Grenoble, France
- 12.5 0.45V and 18μA/MHz MCU SOC with Advanced Adaptive Dynamic Voltage Control (ADVC).....151**
U. Zangi¹, N. Feldman¹, J. Shor², A. Fish²; ¹PLSense, Yokneam Israel, ²Bar Ilan University, Ramat Gan, Israel

SESSION 13: ADVANCED SOI DEVICES 2

Session Chairs:

Olivier Faynot, CEA-Leti

Jiro Ida, Kanazawa Institute of Technology

- 13.1 3D Technologies for Analog/RF Applications.....153**
A. Vandooren, B. Parvais, L. Witters, A. Walke, A. Vais, C. Merckling, D. Lin, N. Waldron, P. Wambacq, D. Mocuta and N. Collaert; imec, Heverlee, Belgium
(Invited Speaker)
- 13.2 Advanced FDSOI Design: The U-Channel Device for 7nm Node and Beyond.....156**
R. Muralidhar, R. Dennard, T. Ando, I. Lauer, and T. Hook; IBM T J Watson Research Center, Yorktown Heights, NY *(Invited Speaker)*
- 13.3 Gate-Induced vs. Implanted Body Doping Impact on Z²-FET DC Operation.....158**
C. Navarro¹, F. Gamiz¹, N. Rodriguez¹, L. Donetti¹, C. Sampedro¹, S. I. Kim², Y. T. Kim², S. Cristoloveanu³; ¹University of Granada, Granada, Spain, ²Korean Institute of Technology, Seoul, Republic of Korea, ³IMEP-LAHC, Grenoble, France
- 13.4 Experimental Comparative Analysis between Junctionless and Inversion Mode Nanowire Transistors Down to 10 nm-Long Channel Lengths.....160**
R. T. Doria¹, R. Trevisoli¹, M. de Souza¹, M. A. Pavanello¹, M. Vinet², M. Cassé², O. Faynot²; ¹Centro Universitário FEI, São Bernardo do Campo, Brazil, ²CEA, LETI, Minatec Campus, Grenoble, France

SESSION 14: LOW POWER CIRCUITS 2

Session Chairs:

Alexander Fish, Bar-Ilan University

Yoshiki Yamamoto, Renesas Electronics Corporation

- 14.1 Blackghost 1.0 Test Chip: On the Road Towards Commercializing Ultra-Low-Vdd SoC for Internet-of-Things.....163**
Y. Pu, K. Easton, C. Shi, R. Beraha, A. Newham, R. Attar and Y. Du; Qualcomm Research *(Invited Speaker)*
- 14.2 Optimizing TSPC Frequency Dividers for Always-On Low-Frequency Applications in 28nm FDSOI CMOS.....165**
P. Xu, C. Gimeno and D. Bol; ECS group, ICTEAM institute, Université catholique de Louvain, Belgium
- 14.3 An Ultra-Low-Power Dual-Phase Latch Based Digital Accelerator for Continuous Monitoring of Wheezing Episodes.....167**
P. Gonzalez-Guerrero and M. Stan; Department of Electrical and Computer Engineering, Charlottesville, Virginia, University of Virginia
- 14.4 An Ultra-Low-Power FPGA for IoT Applications.....169**
H. Qi, O. Ayorinde, and B. H. Calhoun; Dept. of Electrical and Computer Engineering, University of Virginia, Charlottesville, Virginia, USA

SESSION 15: ADVANCED SOI TECHNOLOGY

Session Chairs:

Toshiro Hiramoto, University of Tokyo

Nuo Xu, Samsung

- 15.1 How to Leverage SOI Platforms to Achieve Optimum Power Efficiency?.....N/A**
Manuel Sellier; *Soitec (Invited Speaker)*
- 15.2 Enhanced Design Performance Thanks to Adaptive Body Biasing Technique in FDSOI Technologies.....172**
F. Arnaud¹, S. Clerc¹, S. Haendler¹, R. Bingert¹, P. Flatresse¹, V. Huard¹, T. Poiroux²;
¹STMicroelectronics, Crolles, France, ²CEA-Leti, Minatec Campus, Grenoble, France
(Invited Speaker)

SESSION 16: LOW VOLTAGE DEVICES 1

Session Chairs:

Anne Vandooren, imec

Ramachandran Muralidhar, IBM

- 16.1 New Steep-Slope Device of Comprehensive Properties Enhancement with Hybrid Operation Mechanism for Ultra-Low-Power Applications.....176**
R. Huang, Q. Huang, Y. Zhao, C. Chen, R. Jia, C. Wu, J. Wang, L. Guo and Y. Wang;
Key Laboratory of Microelectronic Devices (MOE), Institute of Microelectronics, Peking University, Peking, Beijing, China and National Key Laboratory of Science and Technology on Micro/Nano Fabrication, Beijing, China (Invited Speaker)
- 16.2 Experimental Analysis of Differential Pairs Designed with Line Tunnel FET Devices.....179**
M. D. V. Martino¹, J. A. Martino¹, P. G. D. Agopian^{1,2}, R. Rooyackers³, E. Simoen³, N. Collaert³, and C. Claeys^{3,4}; ¹LSI/PSI/USP, University of São Paulo, São Paulo, Brazil, ²São Paulo State University (UNESP), Campus São João da Boa Vista, Brazil, ³imec, Leuven, Belgium, ⁴E.E. Dept, KU Leuven, Leuven, Belgium
- 16.3 A 11.5pW/bit 400mV 5T Gain-Cell eDRAM for ULP Applications in 28nm FD-SOI.....182**
R. Gitterman, A. Teman, and A. Fish; *Faculty of Engineering, Bar-Ilan University, Ramat Gan, Israel*
- 16.4 Investigation of Short-Channel Effects in 2D Negative-Capacitance Field-Effect Transistors.....185**
W-X. You, C-P. Tsai, and P. Su; *Department of Electronics Engineering & Institute of Electronics, National Chiao Tung University, Taiwan*
- 16.5 Piezoelectronic Transistor for Low-Voltage High-Speed Integrated Electronics.....188**
S. Sugahara, Y. Shuto, S. Yamamoto, H. Funakubo and M.K. Kurosawa; *Tokyo Institute of Technology, Yokohama, Japan*

SESSION 17: NEUROMORPHIC COMPUTING 1

Session Chairs:

Nuo Xu, Samsung

Olivier Faynot, CEA-Leti

- 17.1 The N3XT Technology for Brain-Inspired Computing.....N/A**
Philip Wong; *Stanford University, Stanford CA, USA (Invited Speaker)*
- 17.2 System-Level Benchmark of Synaptic Device Characteristics for Neuro-Inspired Computing.....190**
P-Y. Chen, X. Peng, and S. Yu; *School of Electrical, Computer and Energy Engineering, Arizona State University, Tempe, AZ (Invited Speaker)*
- 17.3 Machine Intelligence through 3D Waferscale Integration.....192**
A. Kumar and W. Wilcke, *IBM T.J. Watson Research Center, Yorktown Heights, NY, USA (Invited Speaker)*
- 17.4 Three-Dimensional Wafer Scale Integration for Ultra-Large-Scale Cognitive Systems.....194**
Z. Wan and S.S. Iyer; *Center for Heterogenous Integration and Performance Scaling (CHIPS), Electrical and Computer Engineering Department, University of California, Los Angeles, Los Angeles, CA, USA (Invited Speaker)*

SESSION 18: MONOLITHIC 3D 2

Session Chairs:

Jin-Woo Han, NASA

Anne Vandooren, imec

- 18.1 Monolithic Integration of Multiple III-V Semiconductors on Si.....196**
H. Schmid, B. Mayer, J. Gooth, S. Wirths, L. Czornomaz, H. Riel, S. Mauthe, C. Convertino and K. E. Moselund; *IBM Research, Zürich, Switzerland (Invited Speaker)*
- 18.2 GOI Fabrication for Monolithic 3D Integration.....199**
A. Abedin, L. Žurauskaitė, A. Asadollahi, K. Garidis, G. Jayakumar, B.G. Malm, P.-E. Hellström* and M. Östling; *Department of Electronics, KTH Royal Institute of Technology Stockholm, Sweden*
- 18.3 A 1,000x Improvement in Computer Systems by Bridging the Processor-Memory Gap.....202**
Z. Or-Bach; *Monolithic 3D Inc., San Jose, CA*

SESSION 19: NEUROMORPHIC COMPUTING 2

Session Chairs:

Philip Wong, Stanford University

Arvind Kumar, IBM

- 19.1 Analog Circuits for Mixed-Signal Neuromorphic Computing Architectures in 28 nm FD-SOI Technology.....206**
N. Qiao and G. Indiveri; *Institute of Neuroinformatics, University of Zurich and ETH Zurich Zurich, Switzerland (Invited Speaker)*
- 19.2 TrueNorth: from Hardware to Ecosystem.....N/A**
John Arthur; *IBM Research (Invited Speaker)*
- 19.3 High Performance Spiking Neural Net Accelerators for Embedded Computer Vision Applications.....210**
J. K. Kim, P. Knag, T. Chen, C. Liu, C-E. Lee, and Z. Zhang; *Department of Electrical Engineering and Computer Science, University of Michigan, Ann Arbor, MI, USA (Invited Speaker)*

SESSION 20: HETEROGENEOUS INTEGRATION

Session Chairs:

Jeng-Bang Yau, IBM
Nadine Collaert, imec

- 20.1 Neuromorphic Computing with Metal-Oxide Memristors and Floating-Gate Memory Devices.....N/A**
Dimitri Strukov; *University of Santa Barbara, Santa Barbara, CA, USA*
(Invited Speaker)
- 20.2 New Thermal Management Approach for Transistor-Level 3-D Integration.....212**
M. A. Iqbal, M. Rahman; *Computer Science Electrical Engineering, University of Missouri-Kansas City, Kansas City, MO, USA*
- 20.3 Hybrid Silicon CMOS-Carbon Nanotube Physically Uncloable Functions.....215**
D. Armstrong, B. Nasri, R. Karri, and D. Shahrjerdi; *Electrical and Computer Engineering, New York University, Brooklyn, New York*
- 20.4 Die-Level Processing for 3-D Monolithic Integration of Piezoelectric MEMS on CMOS.....218**
A. R. Colon-Berrios, H. Edrees, D. De Godoy, P. Kinget and I. Kyriassis; *Electrical Engineering Department, Columbia University in the City of New York, New York, NY, USA*

SESSION 21: FDSOI CIRCUITS 2

Session Chairs:

Lauri Koskinen, *University of Turku*
Philippe Flatresse, *Soitec*

- 21.1 System Level FDSOI Exploration and Integration.....N/A**
Jeff Cunningham; *NXP Semiconductors (Invited Speaker)*
- 21.2 A 65-nm SOTB Implementation of a Physically Unclonable Function and Its Performance Improvement by Body Bias Control.....221**
Y. Hori, T. Katashita, and Y. Ogasahara; *National Institute of Advanced Industrial Science and Technology (AIST), Tsukuba, Ibaraki, Japan*
- 21.3 Physical Implementation of Low Power SoC Chip Based on SEC 28nm FDS.....224**
J. Zhu, S. Jin, J. Chen; *Customer Silicon Division, VeriSilicon, Inc. Shanghai, China P.R.C*
- 21.4 A 0.148nJ/Conversion 65nm SOTB Temperature Sensor LSI Using Thermistor-Defined Current Source.....228**
S. Nii and K. Ishibashi; *The University of Electro-Communications Tokyo, Japan*
- 21.5 Design Methodology with Body Bias: from Circuit to Engineering.....230**
R. Gomez¹, C. Dutto¹, V. Huard¹, S. Clerc¹, E. Bano², P. Flatresse¹; ¹STMicroelectronics, Crolles, France, ²IMEP-LAHC, Grenoble, France

SESSION 22: PRECISION WAFER BONDING

Session Chairs:

Zvi Or-Bach, *Monolithic 3D*
Bruce Doris, *IBM*

- 22.1 1 μ m Pitch Direct Hybrid Bonding with <300nm Wafer-to-Wafer Overlay Accuracy...234**
A. Jouve¹, V. Balan¹, N. Bresson¹, C. Euvrard-Colnat¹, F. Fournel¹, Y. Exbrayat¹, G. Mauguen¹, M. Abdel Sater¹, C. Beitia¹, L. Arnaud¹, S. Cheramy¹, S. Lhostis², A. Farcy², S. Guillaumet², S. Mermoz²; ¹CEA, LETI, University Grenoble Alpes, Grenoble, France MINATEC Campus, Grenoble, France, ²STMicroelectronics, Crolles, France

22.2 Mass Production Equipment Technology for 300mm Wafer-Level Fusion Bonding.....N/A

T. Kawauchi; *3D-Integration Division, Tokyo Electron Limited (Invited Speaker)*

22.3 TBA.....N/A

M. Jürgen Wolf; *Fraunhofer Institute for Reliability and Microintegration IZM, Berlin, Germany (Invited Speaker)*

SESSION 23: LOW VOLTAGE DEVICES 2

Session Chairs:

Michelly de Souza, *Centro Universitário FEI*

Ru Huang, *Peking University*

23.1 Theoretical Investigation of Backgate-Biasing Effects on Ultrathin-Body GeSn Based Tunneling FET.....236

H. Wang¹, G. Han¹, Y. Liu¹, J. Zhang¹, Y. Hao¹, X. Jiang²; ¹*State Key Discipline Laboratory of Wide Band Gap Semiconductor Technology, School of Microelectronics, Xidian University, Xi'an, Shaanxi, China*, ²*State Key Laboratory of Supperlattices and Microstructures, Institute of Semiconductors, Chinese Academy of Sciences, Beijing China*

23.2 Balancing Pull-In and Adhesion Stability Margins in Non-Volatile NEM Switches...239

G. Usai¹, L. Hutin¹, U. Sikder², J. L. Muñoz-Gamarra¹, T. Ernst¹, T. J. King Liu², M. Vinet¹; ¹*CEA Leti Minatec Campus, Grenoble*, ²*University of California at Berkeley, EECS Department, Berkeley, CA*

23.3 Projected Performance of Experimental InAs/GaAsSb/GaSb TFET as Millimeter-Wave Detector.....241

J. Zhang¹, C. Alessandri¹, P. Fay¹, A. Seabaugh¹, T. Ytterdal², E. Memisevic³ and L. E. Wernersson³; ¹*Department of Electrical Engineering, University of Notre Dame, Notre Dame, IN, USA*, ²*Department of Electronic Systems Norwegian University of Science and Technology Trondheim, Norway*, ³*Department of Electrical and Information Technology, Lund University*

23.4 High-Density SRAM Voltage Scaling Enabled by Inserted-Oxide FinFET Technology.....243

Y-T. Wu¹, M-H. Chiang¹, J. F. Chen¹, F. Ding², D. Connelly², and T-J. King Liu²; ¹*Institute of Microelectronics, Department of Electrical Engineering, National Cheng Kung University, Taiwan, R.O.C.*, ²*Department of Electrical Engineering and Computer Sciences, University of California at Berkeley, CA, USA*

23.5 Analog Performance of Self-Cascode SOI Nanowires nMOSFETs Aiming at Low-Power Applications.....246

R. Assalti¹, M. de Souza¹, M. Cassé², S. Barraud², G. Reimbold², M. Vinet² and O. Faynot²; ¹*Department of Electrical Engineering, Centro Universitário FEI, São Bernardo do Campo, Brazil*, ²*Département des Composants Silicium – SCME/LCTE, CEA-LETI Minatec, Grenoble, France*

SESSION 24: MONOLITHIC 3D 3

Session Chairs:

Jin-Woo Han, NASA

Zvi Or-Bach, Monolithic 3D

- 24.1 Layered Semiconductors for Monolithic 3D Integration.....N/A**
Angada Sachid; *UC Berkeley, Berkeley, CA, USA (Invited Speaker)*
- 24.2 Reliability Analysis on Low Temperature Gate Stack Process Steps for 3D Sequential Integration.....249**
A. Tsiara^{1,2}, X. Garros¹, C.-M. V. Lu¹, C. Fenouillet-Béranger¹, P. Batude¹, R. Gassilloud¹, F. Martin¹, O. Faynot¹, G. Ghibaudo² and G. Reimbold¹; ¹CEA, LETI, MINATEC Campus, ²IMEP-LAHC, Grenoble France
- 24.3 Towards 500°C SPER Activated Devices for 3D Sequential Integration.....252**
J. Micout^{1,2}, B. Sklenard¹, P. Batude¹, R. Berthelon^{1,3}, Q. Rafhay², J. Lacord¹, B. Mathieu¹, L. Pasini^{1,2,3}, Z. Saghi¹, V. Delaye¹, L. Brunet¹, C. Fenouillet-Beranger¹, S. Joblot³, F. Mazen¹, V. Mazzocchi¹, J-P. Colinge¹, G. Ghibaudo² and M. Vinet¹; ¹CEA, Leti, MINATEC Campus, Univ. Grenoble Alpes, ²IMEP-LAHC, MINATEC/INPG, Univ. Grenoble Alpes, ³STMicroelectronics
- 24.4 A Partitioning-Free Methodology for Optimized Gate-Level Monolithic 3D Designs.....254**
O. Billoint¹, M. Brocard¹, S. Thuries¹, G. Berhault¹, H. Sarhan²; ¹Univ. Grenoble Alpes, Grenoble, France, ²MENTOR GRAPHICS, Montbonnot-Saint-Martin, France
- 24.5 Generalized Cost Model for 3D Systems.....256**
D. Gitlin¹, M. Vinet², S. Cheramy², H. Metras², O. Faynot², T. Signamarcheix² and J-R. Lequepeys²; ¹Scientific Advisor & Independent Consultant to CEA-Leti, Palo Alto, CA, ²CEA Leti, MINATEC Campus, Grenoble, France